

Silicon NPN Power Transistors

2SC1106

DESCRIPTION

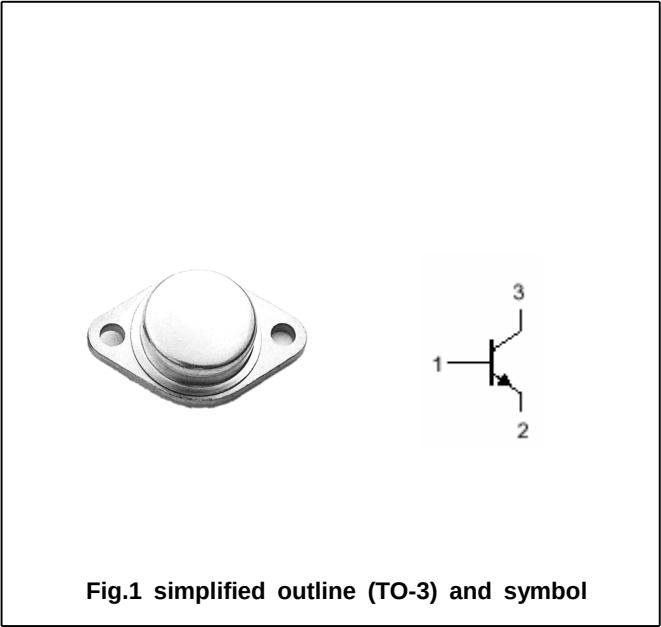
- With TO-3 package
- High power dissipation
- High breakdown voltage

APPLICATIONS

- For voltage regulator ,inverter and switching mode power supply applications

PINNING(see Fig.2)

PIN	DESCRIPTION
1	Base
2	Emitter
3	Collector



Absolute maximum ratings(Ta=?)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V _{CBO}	Collector-base voltage	Open emitter	350	V
V _{CEO}	Collector-emitter voltage	Open base	250	V
V _{EBO}	Emitter-base voltage	Open collector	6	V
I _C	Collector current		2	A
P _C	Collector power dissipation	T _C =25°	80	W
T _j	Junction temperature		150	°
T _{stg}	Storage temperature		-55~150	°

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CHARACTERISTICS

T_j=25° unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{CEO(SUS)}	Collector-emitter sustaining voltage	I _C =0.1A ; I _B =0	250			V
V _{(BR)CBO}	Collector-base breakdown voltage	I _C =1mA ; I _E =0	350			V
V _{(BR)EBO}	Emitter-base breakdown voltage	I _E =1mA ; I _C =0	6			V
V _{CEsat}	Collector-emitter saturation voltage	I _C =1.5A; I _B =0.3A			5.0	V
V _{BESat}	Base-emitter saturation voltage	I _C =1.5A; I _B =0.3A			1.5	V
I _{CBO}	Collector cut-off current	V _{CB} =350V; I _E =0			0.1	mA
I _{EBO}	Emitter cut-off current	V _{EB} =5V; I _C =0			0.1	mA
h _{FE}	DC current gain	I _C =0.2A ; V _{CE} =5V	30			

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PACKAGE OUTLINE

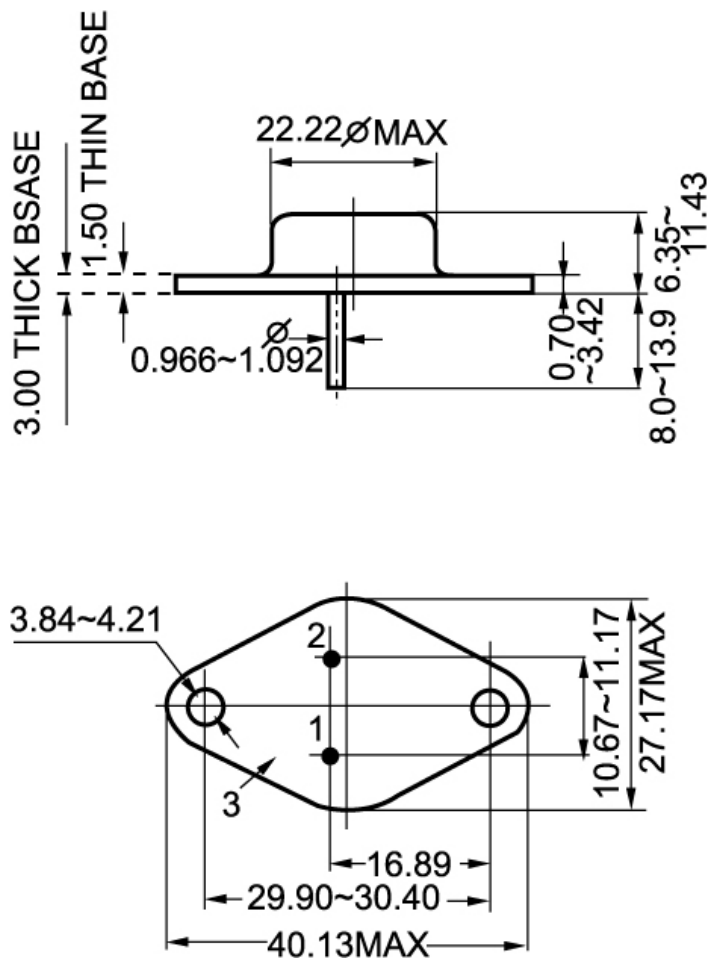


Fig.2 outline dimensions (unindicated tolerance:±0.1mm)